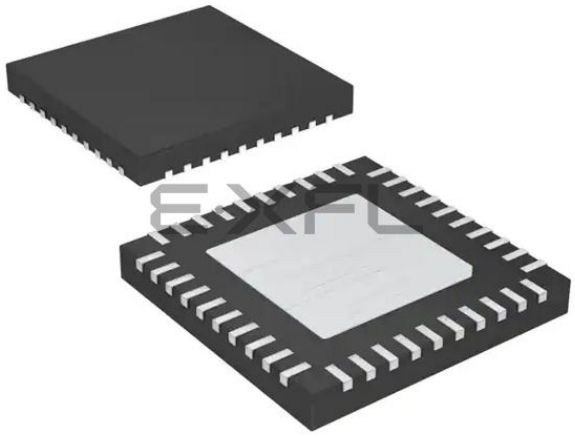
Renesas Electronics America Inc - R5F213M6UNNP#W0 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Last Time Buy
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART, USB
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	30
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	40-WFQFN Exposed Pad
Supplier Device Package	40-HWQFN (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f213m6unnp-w0

1.1.3 Specifications

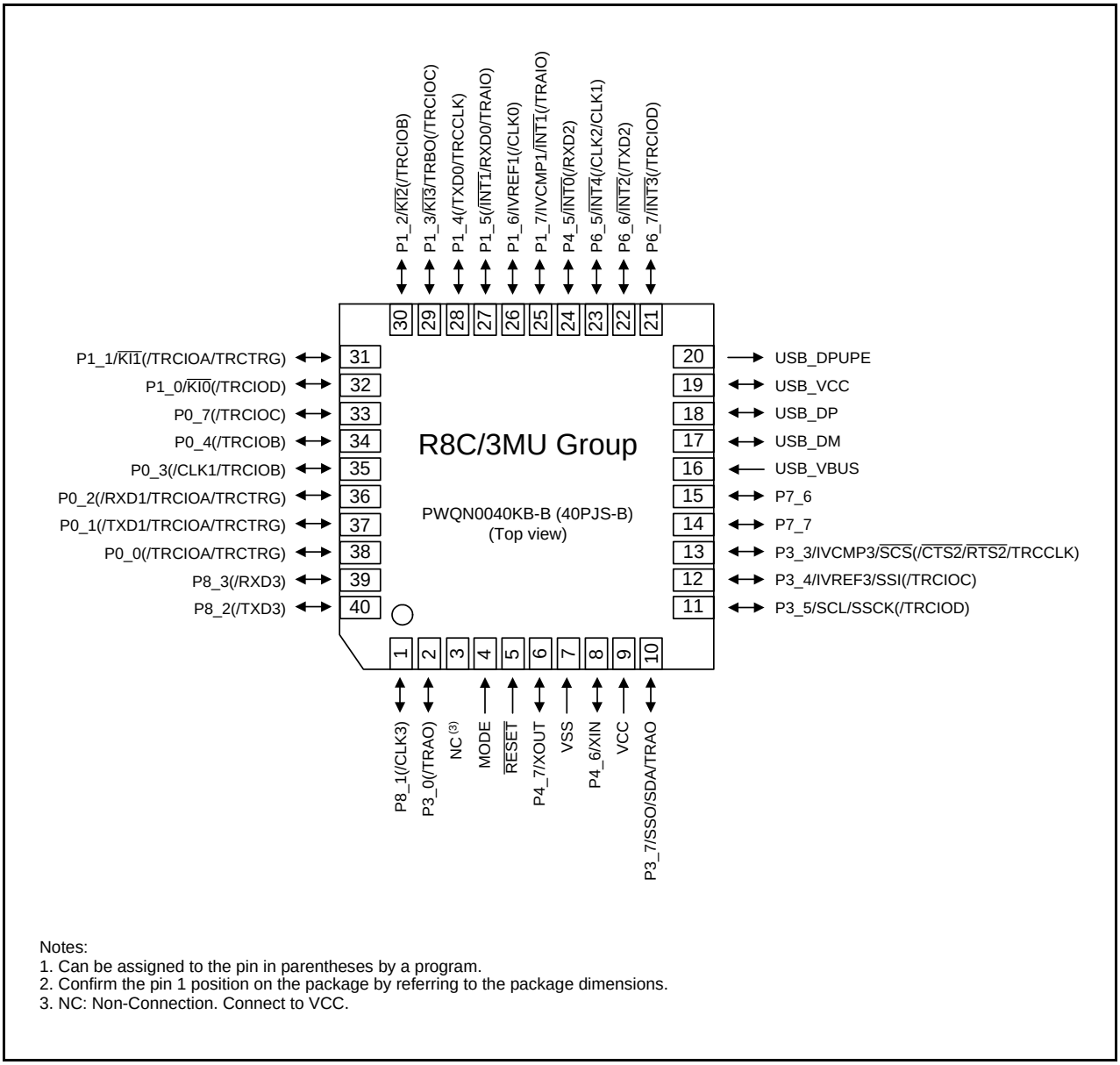
Tables 1.2 and 1.3 outline the Specifications for R8C/3MU Group, R8C/3MK Group.

Table 1.2 Specifications for R8C/3MU Group, R8C/3MK Group (1)

Item	Function	Specification
CPU	Central processing unit	R8C CPU core • Number of fundamental instructions: 89 • Minimum instruction execution time: 50 ns (f(XIN) = 20 MHz, VCC = 2.7 to 5.5 V) 200 ns (f(XIN) = 5 MHz, VCC = 1.8 to 5.5 V) • Multiplier: 16 bits × 16 bits → 32 bits • Multiply-accumulate instruction: 16 bits × 16 bits + 32 bits → 32 bits • Operation mode: Single-chip mode (address space: 1 Mbyte)
Memory	ROM, RAM, Data flash	Refer to **Table 1.4 Product List for R8C/3MU Group**, and **Table 1.5 Product List for R8C/3MK Group**.
Power Supply Voltage Detection	Voltage detection circuit	• Power-on reset • Voltage detection 3 (detection level of voltage detection 0 and voltage detection 1 selectable)
I/O Ports	Programmable I/O ports	• CMOS I/O ports: 30, selectable pull-up resistor • High current drive ports: 30
Clock	Clock generation circuits	• 4 circuits: XIN clock oscillation circuit, High-speed on-chip oscillator (with frequency adjustment function), Low-speed on-chip oscillator PLL frequency synthesizer • Oscillation stop detection: XIN clock oscillation stop detection function • Frequency divider circuit: Dividing selectable 1, 2, 4, 8, and 16 • Low power consumption modes: Standard operating mode (XIN clock, PLL frequency synthesizer, high-speed on-chip oscillator, low-speed on-chip oscillator), wait mode, stop mode
Interrupts		• Interrupt Vectors: 69 • External: 9 sources ($\overline{\text{INT}}$ × 5, key input × 4) • Priority levels: 7 levels
Watchdog Timer		• 14 bits × 1 (with prescaler) • Reset start selectable • Low-speed on-chip oscillator for watchdog timer selectable
DTC (Data Transfer Controller)	R8C/3MU Group	• 1 channel • Activation sources: 25 • Transfer modes: 2 (normal mode, repeat mode)
	R8C/3MK Group	• 1 channel • Activation sources: 26 • Transfer modes: 2 (normal mode, repeat mode)
Timer	Timer RA	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), pulse output mode (output level inverted every period), event counter mode, pulse width measurement mode, pulse period measurement mode
	Timer RB	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), programmable waveform generation mode (PWM output), programmable one-shot generation mode, programmable wait one-shot generation mode
	Timer RC	16 bits × 1 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 3 pins), PWM2 mode (PWM output pin)
Serial Interface	UART0, UART1, UART3	Clock synchronous serial I/O/UART × 3 channel
	UART2	Clock synchronous serial I/O, UART, multiprocessor communication function
Synchronous Serial Communication Unit (SSU)		1 (shared with I^2C bus)
I^2C bus		1 (shared with SSU)
LIN Module		Hardware LIN: 1 (timer RA, UART0)

1.4 Pin Assignment

Figures 1.5 and 1.6 show Pin Assignment (Top View) of Each Group. Table 1.6 outlines the Pin Name Information by Pin Number.



Notes:
1. Can be assigned to the pin in parentheses by a program.
2. Confirm the pin 1 position on the package by referring to the package dimensions.
3. NC: Non-Connection. Connect to VCC.

Figure 1.5 Pin Assignment (Top View) of R8C/3MU Group

1.5 Pin Functions

Tables 1.7 and 1.8 list Pin Functions.

Table 1.7 Pin Functions (1)

Item	Pin Name	I/O Type	Description
Power supply input	VCC, VSS	—	Apply 1.8 to 5.5 V to the VCC pin. Apply 0 V to the VSS pin.
Analog power supply input	AVCC, AVSS (2)	—	Power supply for the A/D converter. Connect a capacitor between AVCC and AVSS.
Reset input	$\overline{\text{RESET}}$	I	Input “L” on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
XIN clock input	XIN	I	These pins are provided for XIN clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins. (1) To use an external clock, input it to the XOUT pin and leave the XIN pin open.
XIN clock output	XOUT	I/O	
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}$ to $\overline{\text{INT4}}$	I	$\overline{\text{INT}}$ interrupt input pins.
Key input interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins.
Timer RA	TRAIO	I/O	Timer RA I/O pin.
	TRAO	O	Timer RA output pin.
Timer RB	TRBO	O	Timer RB output pin.
Timer RC	TRCCLK	I	External clock input pin.
	TRCTRG	I	External trigger input pin.
	TRCIOA, TRCIOB, TRCIOC, TRCIOD	I/O	Timer RC I/O pins.
Serial interface	CLK0, CLK1, CLK2, CLK3	I/O	Transfer clock I/O pins.
	RXD0, RXD1, RXD2, RXD3	I	Serial data input pins.
	TXD0, TXD1, TXD2, TXD3	O	Serial data output pins.
	$\overline{\text{CTS2}}$	I	Transmission control input pin.
	$\overline{\text{RTS2}}$	O	Reception control output pin.
SSU	SSI	I/O	Data I/O pin.
	$\overline{\text{SCS}}$	I/O	Chip-select signal I/O pin.
	SSCK	I/O	Clock I/O pin.
	SSO	I/O	Data I/O pin.
I^2C bus	SCL	I/O	Clock I/O pin.
	SDA	I/O	Data I/O pin.

I: Input O: Output I/O: Input and output

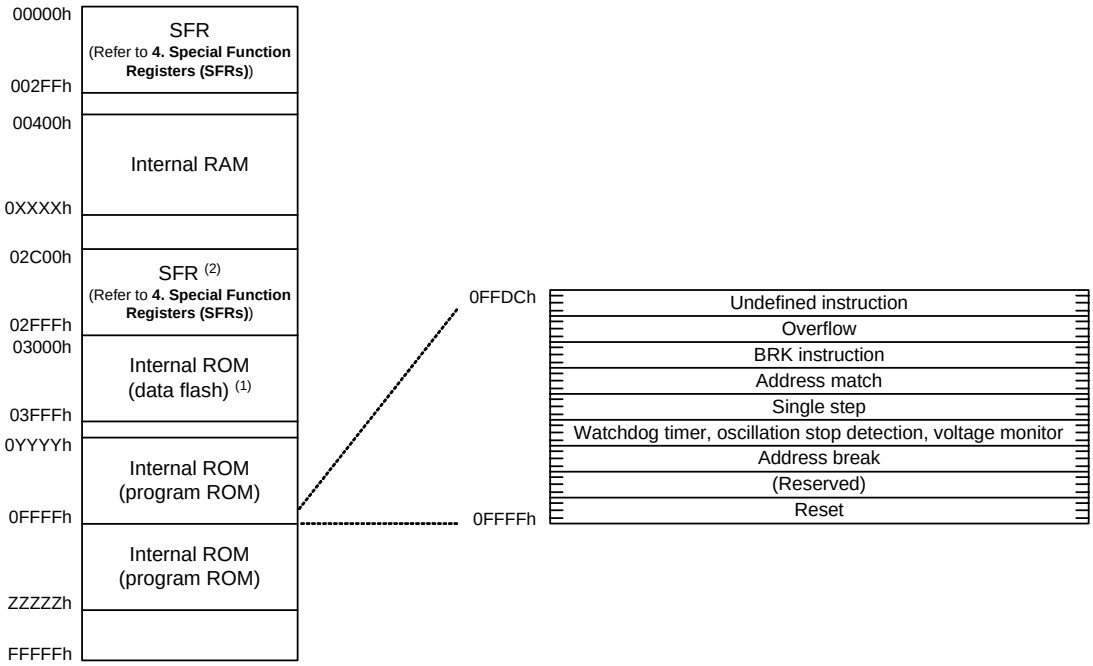
Notes:

1. Refer to the oscillator manufacturer for oscillation characteristics.
2. This pin is not available in the R8C/3MU Group.

3. Memory

3.1 R8C/3MU Group

Figure 3.2 is a Memory Map of R8C/3MU Group. The R8C/3MU Group has a 1-Mbyte address space from addresses 00000h to FFFFFh. For example, a 64-Kbyte internal ROM area is allocated addresses 04000h to 13FFFh. The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. The starting address of each interrupt routine is stored here.
The internal ROM (data flash) is allocated addresses 03000h to 03FFFh.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 8-Kbyte internal RAM area is allocated addresses 00400h to 023FFh. The internal RAM is used not only for data storage but also as a stack area when a subroutine is called or when an interrupt request is acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh and 02C00h to 02FFFh (the SFR areas for the DTC and other modules). Peripheral function control registers are allocated here. All unallocated spaces within the SFRs are reserved and cannot be accessed by users.



Notes:
1. The data flash indicates block A (1 Kbyte), block B (1 Kbyte), block C (1 Kbyte), and block D (1 Kbyte).
2. The SFR areas for the DTC and other modules are allocated to addresses 02C00h to 02FFFh.
3. The blank areas are reserved and cannot be accessed by users.

Part Number	Internal ROM			Internal RAM	
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh
R5F213M6UNNP R5F213M6UNXXXNP	32 Kbytes	08000h	—	4 Kbytes	013FFh
R5F213M8UNNP R5F213M8UNXXXNP	64 Kbytes	04000h	13FFFh	8 Kbytes	023FFh

Figure 3.1 Memory Map of R8C/3MU Group

Table 4.15 SFR Information (15) (1)

Address	Register	Symbol	After Reset
2F00h	USB Module Control Register	USBMC	00X10000b
2F01h	PLL Control Register 0	PLC0	0010X000b
2F02h	PLL Control Register 1	PLC1	00001100b
2F03h	PLL Division Control Register	PLDIV	00001011b
2F04h			
2F05h			
2F06h			
2F07h			
2F08h			
2F09h			
2F0Ah			
2F0Bh			
2F0Ch			
2F0Dh			
2F0Eh			
2F0Fh			
2F10h	USB Pin Select Register 0	USBSR0	00h
2F11h			
2F12h	UART3 Pin Select Register	U3SR	00h
2F13h			
2F14h			
2F15h			
2F16h			
2F17h			
2F18h			
2F19h			
2F1Ah			
2F1Bh			
2F1Ch			
2F1Dh			
2F1Eh			
2F1Fh			
:			
2FFFh			

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.16 ID Code Areas and Option Function Select Area

Address	Area Name	Symbol	After Reset
:			
FFDBh	Option Function Select Register 2	OFS2	(Note 1)
:			
FFDFh	ID1		(Note 2)
:			
FFE3h	ID2		(Note 2)
:			
FFEBh	ID3		(Note 2)
:			
FFEFh	ID4		(Note 2)
:			
FFF3h	ID5		(Note 2)
:			
FFF7h	ID6		(Note 2)
:			
FFFBh	ID7		(Note 2)
:			
FFFFh	Option Function Select Register	OFS	(Note 1)

Notes:

1. The option function select area is allocated in the flash memory, not in the SFRs. Set appropriate values as ROM data by a program.
   Do not write additions to the option function select area. If the block including the option function select area is erased, the option function select area is set to FFh.
   When blank products are shipped, the option function select area is set to FFh. It is set to the written value after written by the user.
   When factory-programming products are shipped, the value of the option function select area is the value programmed by the user.
2. The ID code areas are allocated in the flash memory, not in the SFRs. Set appropriate values as ROM data by a program.
   Do not write additions to the ID code areas. If the block including the ID code areas is erased, the ID code areas are set to FFh.
   When blank products are shipped, the ID code areas are set to FFh. They are set to the written value after written by the user.
   When factory-programming products are shipped, the value of the ID code areas is the value programmed by the user.

Table 5.2 Recommended Operating Conditions (1)

Symbol	Parameter				Conditions	Standard			Unit
						Min.	Typ.	Max.	
V_{CC}	Supply voltage	When USB function is used				3.0	5.0	5.5	V
		When USB function is not used				1.8	5.0	5.5	V
UV_{CC}	USB Supply Voltage (When UVCC pin is input)	When USB function is used			V_{CC} = 3.0 to 3.6 V	—	V_{CC} (4)	—	V
		When USB function is not used			V_{CC} = 1.8 to 5.5 V	—	V_{CC} (4)	—	V
V_{SS}	Supply voltage					—	0	—	V
V_{IH}	Input “H” voltage	Other than CMOS input				0.8 V_{CC}	—	V_{CC}	V
		CMOS input	Input level switching function (I/O port)	Input level selection: 0.35 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.5 V_{CC}	—	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.55 V_{CC}	—	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.65 V_{CC}	—	V_{CC}	V
				Input level selection: 0.5 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.65 V_{CC}	—	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.7 V_{CC}	—	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.8 V_{CC}	—	V_{CC}	V
				Input level selection: 0.7 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.85 V_{CC}	—	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.85 V_{CC}	—	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.85 V_{CC}	—	V_{CC}	V
		External clock input (XOUT)				1.2	—	V_{CC}	V
V_{IL}	Input “L” voltage	Other than CMOS input				0	—	0.2 V_{CC}	V
		CMOS input	Input level switching function (I/O port)	Input level selection: 0.35 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	—	0.2 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	—	0.2 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	—	0.2 V_{CC}	V
				Input level selection: 0.5 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	—	0.4 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	—	0.3 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	—	0.2 V_{CC}	V
				Input level selection: 0.7 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	—	0.55 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	—	0.45 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	—	0.35 V_{CC}	V
		External clock input (XOUT)				0	—	0.4	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH(peak)}$				—	—	−160	mA
$I_{OH(sum)}$	Average sum output “H” current	Sum of all pins $I_{OH(avg)}$				—	—	−80	mA
$I_{OH(peak)}$	Peak output “H” current	Drive capacity Low				—	—	−10	mA
		Drive capacity High				—	—	−40	mA
$I_{OH(avg)}$	Average output “H” current	Drive capacity Low				—	—	−5	mA
		Drive capacity High				—	—	−20	mA
$I_{OL(sum)}$	Peak sum output “L” current	Sum of all pins $I_{OL(peak)}$				—	—	160	mA
$I_{OL(sum)}$	Average sum output “L” current	Sum of all pins $I_{OL(avg)}$				—	—	80	mA
$I_{OL(peak)}$	Peak output “L” current	Drive capacity Low				—	—	10	mA
		Drive capacity High				—	—	40	mA
$I_{OL(avg)}$	Average output “L” current	Drive capacity Low				—	—	5	mA
		Drive capacity High				—	—	20	mA
$f_{(XIN)}$	XIN clock input oscillation frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz
fOCO40M	When used as the count source for timer RC (3)				2.7 V ≤ V_{CC} ≤ 5.5 V	32	—	40	MHz
fOCO-F	fOCO-F frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz
—	System clock frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz
$f_{(BCLK)}$	CPU clock frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz
$t_{su(PLL)}$	PLL frequency symthesizer stabilization wait time				4.0 V ≤ V_{CC} ≤ 5.5 V	—	—	2	ms
					2.7 V ≤ V_{CC} < 4.0 V	—	—	3	ms

Notes:
1. V_{CC} = 1.8 to 5.5 V and T_{opr} = −20 to 85 °C (N version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.
3. fOCO40M can be used as the count source for timer RC in the range of V_{CC} = 2.7 to 5.5 V.
4. Connect V_{CC} for the UV_{CC} pin input.

Table 5.6 Flash Memory (Data flash Block A to Block D) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance (2)		10,000 (3)	—	—	times
—	Byte program time (program/erase endurance ≤ 1,000 times)		—	160	1500	µs
—	Byte program time (program/erase endurance > 1,000 times)		—	300	1500	µs
—	Block erase time (program/erase endurance ≤ 1,000 times)		—	0.2	1	s
—	Block erase time (program/erase endurance > 1,000 times)		—	0.3	1	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	µs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly stopped until reading is enabled		–	–	30 + CPU clock × 1 cycle	µs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		–20	—	85	°C
—	Data hold time (7)	Ambient temperature = 55 °C	20	—	—	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = –20 to 85 °C (N version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed.)
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

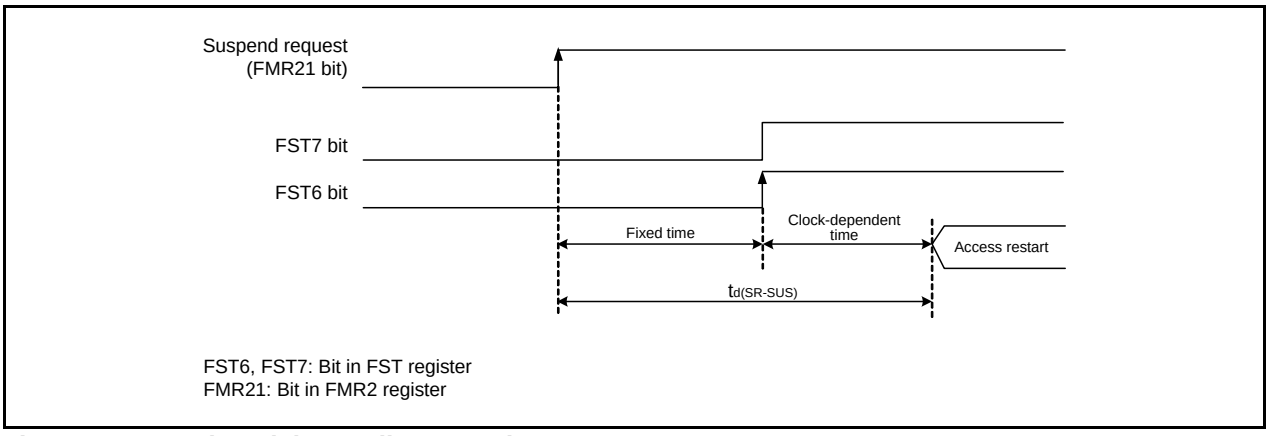


Figure 5.4 Time delay until Suspend

Table 5.9 Voltage Detection 2 Circuit Electrical Characteristics

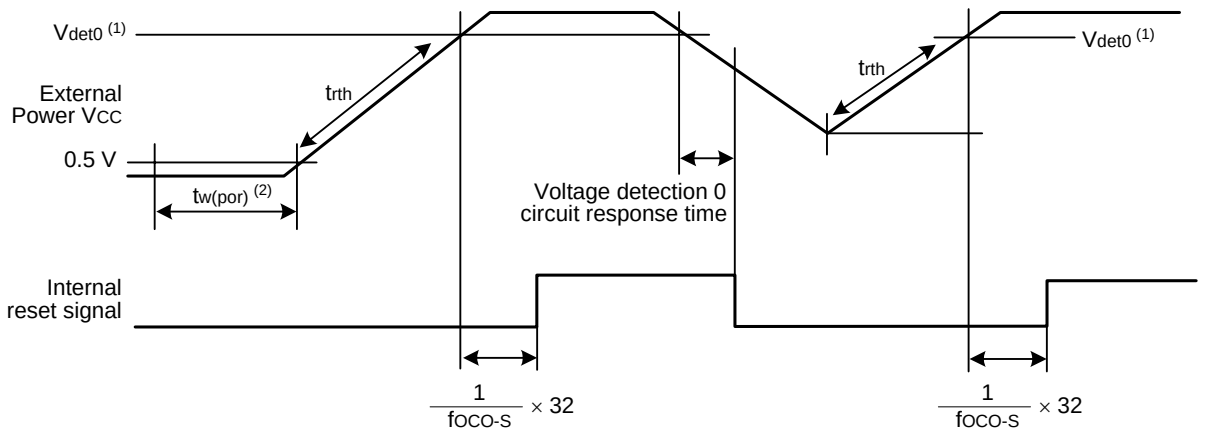
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level Vdet2_0	At the falling of V_{CC}	3.70	4.00	4.30	V
—	Hysteresis width at the rising of V_{CC} in voltage detection 2 circuit		—	0.10	—	V
—	Voltage detection 2 circuit response time (2)	At the falling of V_{CC} from 5.0 V to (Vdet2_0 – 0.1) V	—	20	150	µs
—	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	—	1.7	—	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (3)		—	—	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version).
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.10 Power-on Reset Circuit (2)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t_{rth}	External power V_{CC} rise gradient	(1)	0	—	50,000	mV/msec

Notes:
1. The measurement condition is T_{opr} = –20 to 85 °C (N version), unless otherwise specified.
2. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVDAS bit in the OFS register to 0.



Notes:
1. V_{det0} indicates the voltage detection level of the voltage detection 0 circuit. Refer to **6. Voltage Detection Circuit** of User's Manual: Hardware for details.
2. $t_{w(por)}$ indicates the duration the external power V_{CC} must be held below the valid voltage (0.5 V) to enable a power-on reset. When turning on the power after it falls with voltage monitor 0 reset disabled, maintain $t_{w(por)}$ for 1 ms or more.

Figure 5.5 Power-on Reset Circuit Electrical Characteristics

Table 5.11 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
—	High-speed on-chip oscillator frequency after reset	V_{CC} = 1.8 V to 5.5 V	36.0	40	44.0	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register (2)	V_{CC} = 1.8 V to 5.5 V	33.178	36.864	40.550	MHz
	High-speed on-chip oscillator frequency when the FRA6 register correction value is written into the FRA1 register and the FRA7 register correction value into the FRA3 register	V_{CC} = 1.8 V to 5.5 V	28.8	32	35.2	MHz
—	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	0.5	3	ms
—	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	400	—	µA

Notes:
1. V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version), unless otherwise specified.
2. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.12 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		60	125	250	kHz
—	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	30	100	µs
—	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	2	—	µA

Note:
1. V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version), unless otherwise specified.

Table 5.13 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on (2)		—	—	2,000	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = 25 °C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.

Table 5.14 Timing Requirements of Synchronous Serial Communication Unit (SSU)

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
t_{SUCYC}	SSCK clock cycle time			4	—	—	t_{CYC} (2)
t_{HI}	SSCK clock “H” width			0.4	—	0.6	t_{SUCYC}
t_{LO}	SSCK clock “L” width			0.4	—	0.6	t_{SUCYC}
t_{RISE}	SSCK clock rising time	Master		—	—	1	t_{CYC} (2)
		Slave		—	—	1	µs
t_{FALL}	SSCK clock falling time	Master		—	—	1	t_{CYC} (2)
		Slave		—	—	1	µs
t_{SU}	SSO, SSI data input setup time			100	—	—	ns
t_{H}	SSO, SSI data input hold time			1	—	—	t_{CYC} (2)
t_{LEAD}	$\overline{SCS}$ setup time	Slave		$1t_{CYC}$ + 50	—	—	ns
t_{LAG}	$\overline{SCS}$ hold time	Slave		$1t_{CYC}$ + 50	—	—	ns
t_{OD}	SSO, SSI data output delay time			—	—	1	t_{CYC} (2)
t_{SA}	SSI slave access time		2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	$1.5t_{CYC}$ + 100	ns
			1.8 V ≤ V_{CC} < 2.7 V	—	—	$1.5t_{CYC}$ + 200	ns
t_{OR}	SSI slave out open time		2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	$1.5t_{CYC}$ + 100	ns
			1.8 V ≤ V_{CC} < 2.7 V	—	—	$1.5t_{CYC}$ + 200	ns

Notes:
1. V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V, and T_{opr} = –20 to 85 °C (N version), unless otherwise specified.
2. $1t_{CYC}$ = 1/f1(s)

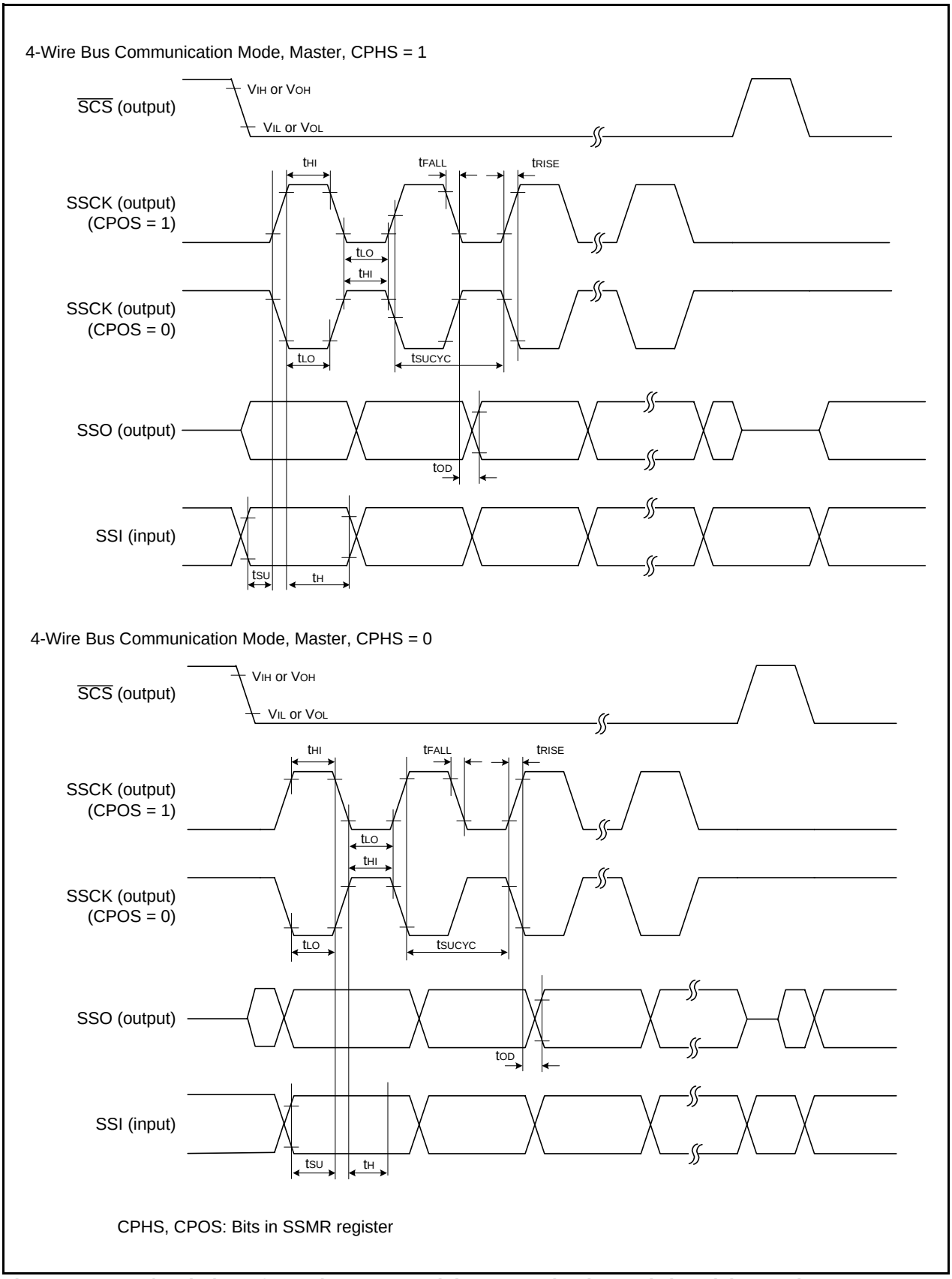


Figure 5.6 I/O Timing of Synchronous Serial Communication Unit (SSU) (Master)

Table 5.17 Electrical Characteristics (2) [3.3 V ≤ Vcc ≤ 5.5 V] (Topr = –20 to 85 °C (N version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	6.5	15	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	5.3	12.5	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	3.6	—	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	3.0	—	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	2.2	—	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	1.5	—	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	—	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	3.0	—	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16, MSTIIC=MSTTRC=1	—	1	—	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	—	90	400	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	15	100	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	4	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	3.5	—	µA
		Stop mode	XIN clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	2.0	5.0	µA
			XIN clock off, Topr = 85 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	15	—	µA

Table 5.22 Electrical Characteristics (3) [2.7 V ≤ Vcc < 4.2 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –5 mA	V_{CC} – 0.5	—	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	—	V_{CC}	V
		XOUT		I_{OH} = –200 μA	1.0	—	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 5 mA	—	—	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	—	—	0.5	V
		XOUT		I_{OL} = 200 μA	—	—	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, USB_VBUS, TRCTRG, TRCCLK, RXD0, RXD1, RXD2, RXD3, CLK0, $\overline{CLK1}$, CLK2, CLK3, $\overline{CTS2}$, SSI, SCL, SDA, SSO, SSCK, $\overline{SCS}$	V_{CC} = 3.0 V		0.1	0.4	—	V
		$\overline{RESET}$	V_{CC} = 3.0 V		0.1	0.5	—	V
I_{IH}	Input “H” current		V_I = 3 V, V_{CC} = 3.0 V		—	—	4.0	μA
I_{IL}	Input “L” current		V_I = 0 V, V_{CC} = 3.0 V		—	—	–4.0	μA
R_{PULLUP}	Pull-up resistance		V_I = 0 V, V_{CC} = 3.0 V		42	84	168	kΩ
R_{fXIN}	Feedback resistance	XIN			—	0.3	—	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Note:
1. 2.7 V ≤ V_{CC} < 4.2 V, T_{opr} = –20 to 85 °C (N version), and f(XIN) = 10 MHz, unless otherwise specified.
2. 3.0 V ≤ V_{CC} < 3.6 V for the USB associated pins.

Table 5.39 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance (2)		1,000 (3)	—	—	times
—	Byte program time		—	80	500	µs
—	Block erase time		—	0.3	—	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	µs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly stopped until reading is enabled		–	–	30 + CPU clock × 1 cycle	µs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		0	—	60	°C
—	Data hold time (7)	Ambient temperature = 55 °C	20	—	—	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = 0 to 60 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed.)
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.41 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level Vdet0_0 (2)		1.80	1.90	2.05	V
	Voltage detection level Vdet0_1 (2)		2.15	2.35	2.50	V
	Voltage detection level Vdet0_2 (2)		2.70	2.85	3.05	V
	Voltage detection level Vdet0_3 (2)		3.55	3.80	4.05	V
—	Voltage detection 0 circuit response time (4)	At the falling of V_{CC} from 5.0 V to (Vdet0_0 – 0.1) V	—	6	150	µs
—	Voltage detection circuit self power consumption	VCA25 = 1, V_{CC} = 5.0 V	—	1.5	—	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (3)		—	—	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version).
2. Select the voltage detection level with bits VDSEL0 and VDSEL1 in the OFS register.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.
4. Time until the voltage monitor 0 reset is generated after the voltage passes V_{det0}.

Table 5.42 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level Vdet1_0 (2)	At the falling of V_{CC}	2.00	2.20	2.40	V
	Voltage detection level Vdet1_1 (2)	At the falling of V_{CC}	2.15	2.35	2.55	V
	Voltage detection level Vdet1_2 (2)	At the falling of V_{CC}	2.30	2.50	2.70	V
	Voltage detection level Vdet1_3 (2)	At the falling of V_{CC}	2.45	2.65	2.85	V
	Voltage detection level Vdet1_4 (2)	At the falling of V_{CC}	2.60	2.80	3.00	V
	Voltage detection level Vdet1_5 (2)	At the falling of V_{CC}	2.75	2.95	3.15	V
	Voltage detection level Vdet1_6 (2)	At the falling of V_{CC}	2.85	3.10	3.40	V
	Voltage detection level Vdet1_7 (2)	At the falling of V_{CC}	3.00	3.25	3.55	V
	Voltage detection level Vdet1_8 (2)	At the falling of V_{CC}	3.15	3.40	3.70	V
	Voltage detection level Vdet1_9 (2)	At the falling of V_{CC}	3.30	3.55	3.85	V
	Voltage detection level Vdet1_A (2)	At the falling of V_{CC}	3.45	3.70	4.00	V
	Voltage detection level Vdet1_B (2)	At the falling of V_{CC}	3.60	3.85	4.15	V
	Voltage detection level Vdet1_C (2)	At the falling of V_{CC}	3.75	4.00	4.30	V
	Voltage detection level Vdet1_D (2)	At the falling of V_{CC}	3.90	4.15	4.45	V
	Voltage detection level Vdet1_E (2)	At the falling of V_{CC}	4.05	4.30	4.60	V
	Voltage detection level Vdet1_F (2)	At the falling of V_{CC}	4.20	4.45	4.75	V
—	Hysteresis width at the rising of V_{CC} in voltage detection 1 circuit	Vdet1_0 to Vdet1_5 selected	—	0.07	—	V
		Vdet1_6 to Vdet1_F selected	—	0.10	—	V
—	Voltage detection 1 circuit response time (3)	At the falling of V_{CC} from 5.0 V to (Vdet1_0 – 0.1) V	—	60	150	µs
—	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	—	1.7	—	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (4)		—	—	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version).
2. Select the voltage detection level with bits VD1S0 to VD1S3 in the VD1LS register.
3. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
4. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

Table 5.51 Electrical Characteristics (2) [3.3 V ≤ Vcc ≤ 5.5 V]
(Topr = –20 to 85 °C (N version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	6.5	15	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	5.3	12.5	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	3.6	—	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	3.0	—	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	2.2	—	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	1.5	—	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	—	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	3.0	—	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16, MSTIIC = MSTTRC = 1	—	1	—	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	—	90	400	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	15	100	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	4	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	3.5	—	µA
		Stop mode	XIN clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	2.0	5.0	µA
			XIN clock off, Topr = 85 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	15	—	µA

Table 5.54 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	—	ns
$t_{W(CKH)}$	CLKi input “H” width	100	—	ns
$t_{W(CKL)}$	CLKi input “L” width	100	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	50	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

i = 0 to 3

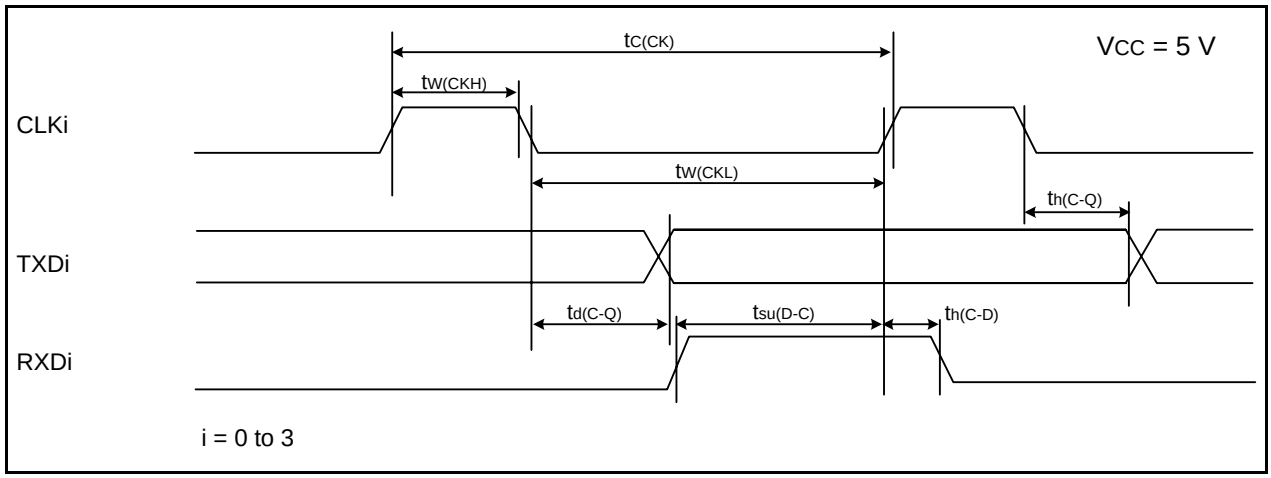


Figure 5.33 Serial Interface Timing Diagram when Vcc = 5 V

Table 5.55 External Interrupt $\overline{INTi}$ (i = 0 to 4) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	250 (1)	—	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	250 (2)	—	ns

Notes:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

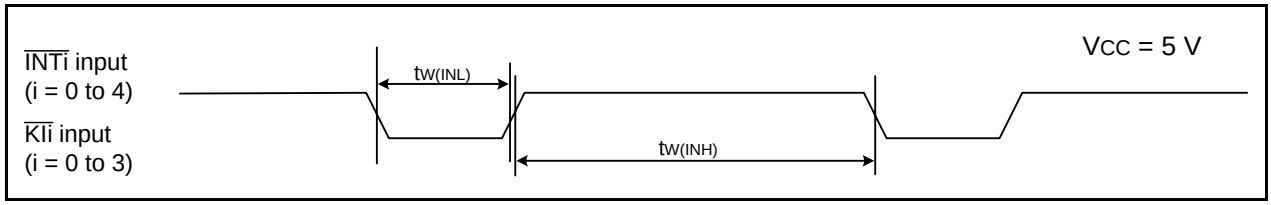


Figure 5.34 Input Timing Diagram for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{KIi}$ when Vcc = 5 V

Timing requirements (Unless Otherwise Specified: V_{CC} = 3 V, V_{SS} = 0 V, T_{opr} = 25 °C)

Table 5.58 External Clock Input (XOUT)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XOUT)}$	XOUT input cycle time	50	—	ns
$t_{WH(XOUT)}$	XOUT input “H” width	24	—	ns
$t_{WL(XOUT)}$	XOUT input “L” width	24	—	ns

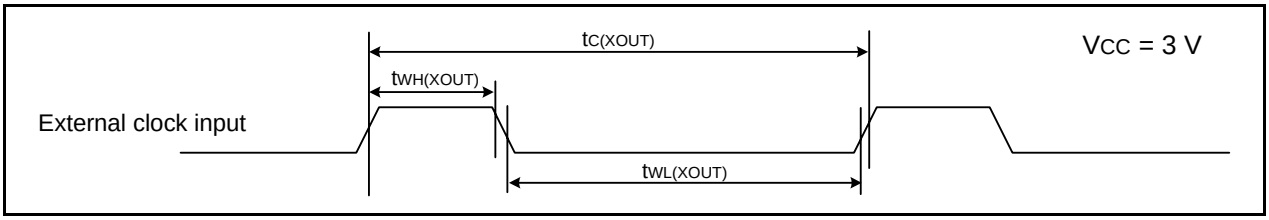


Figure 5.35 External Clock Input Timing Diagram when V_{CC} = 3 V

Table 5.59 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	300	—	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	120	—	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	120	—	ns

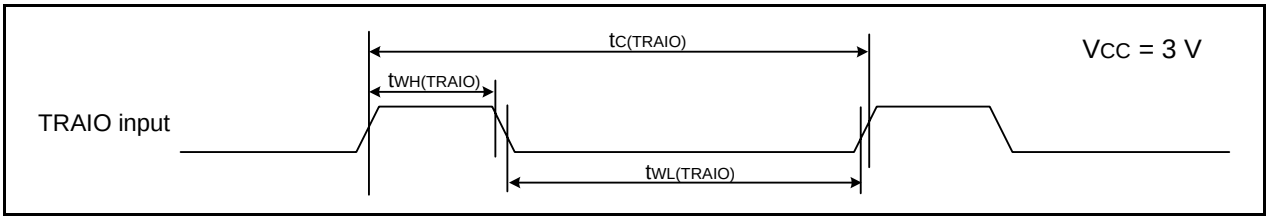


Figure 5.36 TRAIO Input Timing Diagram when V_{CC} = 3 V

Table 5.63 Electrical Characteristics (6) [1.8 V ≤ Vcc < 2.7 V] (Topr = –20 to 85 °C (N version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 1.8 to 2.7 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	2.2	—	mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	0.8	—	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	—	2.5	10	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	1.7	—	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16, MSTIIC = MSTTRC = 1	—	1	—	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	—	90	300	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	15	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	4	80	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	3.5	—	µA
		Stop mode	XIN clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	2.0	5	µA
			XIN clock off, Topr = 85 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	15	—	µA

Table 5.66 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	800	—	ns
$t_{W(CKH)}$	CLKi input “H” width	400	—	ns
$t_{W(CKL)}$	CLKi input “L” width	400	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	200	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	150	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

i = 0 to 3

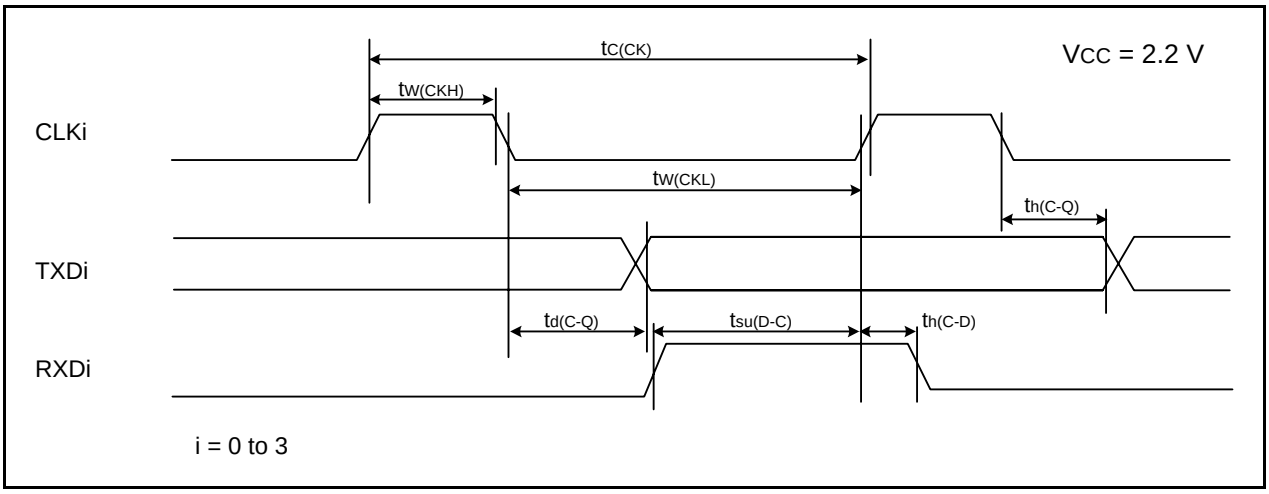


Figure 5.41 Serial Interface Timing Diagram when Vcc = 2.2 V

Table 5.67 External Interrupt $\overline{INTi}$ (i = 0 to 4) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	1000 (1)	—	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	1000 (2)	—	ns

Notes:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

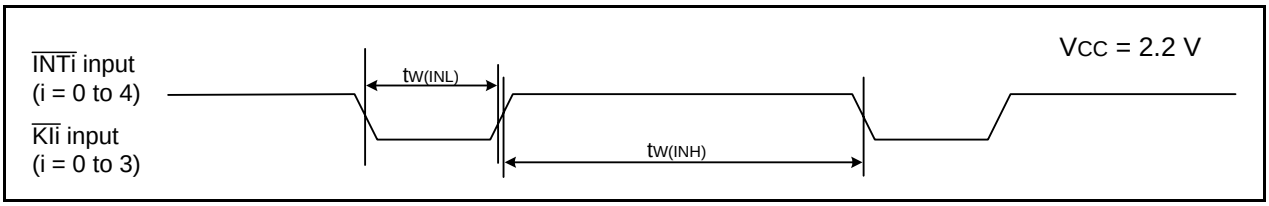


Figure 5.42 Input Timing Diagram for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{KIi}$ when Vcc = 2.2 V